

SAMSUNG SEMICONDUCTOR INC 14E D 7964142 0007236 9

MMBA812M7 PNP EPITAXIAL SILICON TRANSISTOR

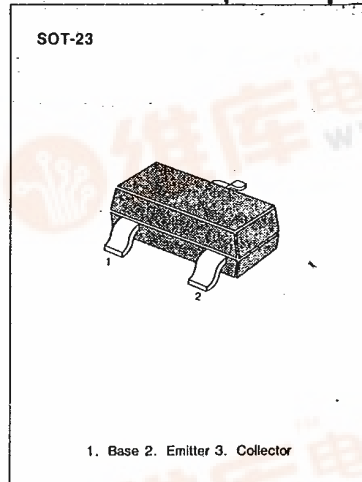
GENERAL PURPOSE TRANSISTOR

T-27-09

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	40	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _c	100	mA
Collector Dissipation	P _c	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I _{cB0}	V _{CB} =40V, I _E =0		100	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0		100	nA
DC Current Gain	h _{FE}	V _{CE} =6V, I _C =1mA	300	600	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C =30mA, I _B =3mA		0.5	V
Base-Emitter On Voltage	V _{BE (on)}	I _C =1mA, V _{CE} =6V		0.8	V

Marking

